Advanced Power MOSFET

SSF7N90A

FEATURES

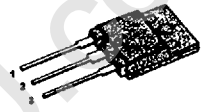
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : 25 μA (Max.) @ V_{DS} = 900V
- Low $R_{DS(ON)}$: 1.247 Ω (Typ.)

BV_{DSS} = 900 V

$R_{DS(on)}$ = 1.8 Ω

I_D = 5 A

TO-3PF



1.Gate 2. Drain 3. Source

Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
V_{DSS}	Drain-to-Source Voltage	900	V
I_D	Continuous Drain Current (T_C=25 ℃)	5	A
	Continuous Drain Current (T_C=100 ℃)	3.2	
I_{DM}	Drain Current-Pulsed ①	28	A
V_{GS}	Gate-to-Source Voltage	±30	V
E_{AS}	Single Pulsed Avalanche Energy ②	794	mJ
I_{AR}	Avalanche Current ①	5	A
E_{AR}	Repetitive Avalanche Energy ①	9.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	1.5	V/ns
P_D	Total Power Dissipation (T_C=25 ℃)	95	W
	Linear Derating Factor	0.76	W/ ℃
T_J , T_{STG}	Operating Junction and Storage Temperature Range	- 55 to +150	℃
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8 " from case for 5-seconds	300	

Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	1.32	℃/W
$R_{\theta JA}$	Junction-to-Ambient	--	40	

SAMSUNG ELECTRONICS

Electrical Characteristics (T_C=25• •unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV_{DSS}	Drain-Source Breakdown Voltage	900	--	--	V	V_{GS}=0V,I_D=250• A
• BV/• T_J	Breakdown Voltage Temp. Coeff.	--	1.06	--	V/• •	I_D=250• A *See Fig 7*
$V_{GS(th)}$	Gate Threshold Voltage	2.0	--	3.5	V	V_{DS}=5V,I_D=250• A
I_{GSS}	Gate-Source Leakage , Forward	--	--	100	nA	V_{GS}=30V
	Gate-Source Leakage , Reverse	--	--	-100		V_{GS}=-30V
I_{DSS}	Drain-to-Source Leakage Current	--	--	25	• A	V_{DS}=900V
		--	--	250		V_{DS}=720V,T_C=125• •
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	1.8	• •	V_{GS}=10V,I_D=2.5A • •*
g_{fs}	Forward Transconductance	--	4.72	--	•	V_{DS}=50V,I_D=2.5A • •
C_{iss}	Input Capacitance	--	2070	2690	pF	V_{GS}=0V,V_{DS}=25V,f =1MHz *See Fig 5*
C_{oss}	Output Capacitance	--	185	215		
C_{rss}	Reverse Transfer Capacitance	--	78	90		
$t_{d(on)}$	Turn-On Delay Time	--	25	60	ns	V_{DD}=450V,I_D=8A, R_G=10• • *See Fig 13* • ▬ •
t_r	Rise Time	--	38	85		
$t_{d(off)}$	Turn-Off Delay Time	--	122	255		
t_f	Fall Time	--	41	90		
Q_g	Total Gate Charge	--	94	123	nC	V_{DS}=720V,V_{GS}=10V, I_D=8A *See Fig 6 & Fig 12* • ▬ •
Q_{gs}	Gate-Source Charge	--	14.9	--		
Q_{gd}	Gate-Drain(• iller• •Charge	--	43.5	--		

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I_S	Continuous Source Current	--	--	5	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current • •	--	--	28		
V_{SD}	Diode Forward Voltage • •	--	--	1.4	V	T_J=25• ,I_S=5A,V_{GS}=0V
t_{rr}	Reverse Recovery Time	--	620	--	ns	T_J=25• ,I_F=8A
Q_{rr}	Reverse Recovery Charge	--	9.3	--	• C	di_F/dt=100A/• s • •

Notes ;

- • •Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- • •L=60mH, I_{AS}=5A, V_{DD}=50V, R_G=27• ; Starting T_J=25• •
- • •I_{SD}• 8A, di/dt• 170A/• s, V_{DD}• BV_{DSS}, Starting T_J=25• •
- • •Pulse Test : Pulse Width = 250• s, Duty Cycle • 2%
- • •Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

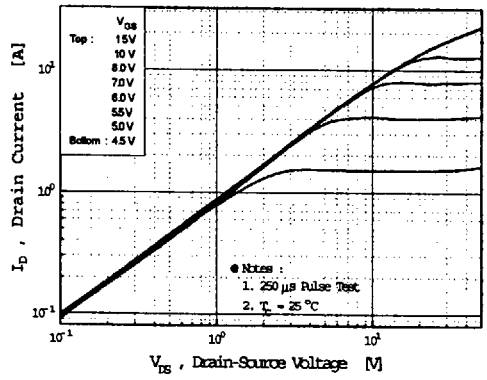


Fig 2. Transfer Characteristics

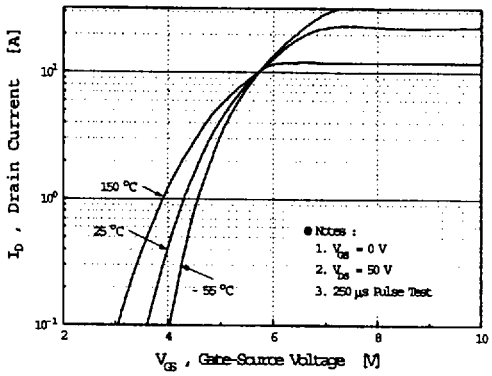


Fig 3. On-Resistance vs. Drain Current

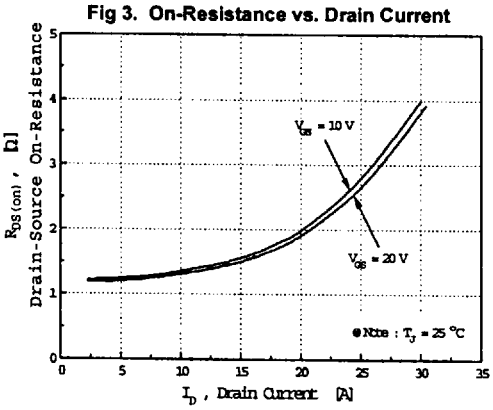


Fig 4. Source-Drain Diode Forward Voltage

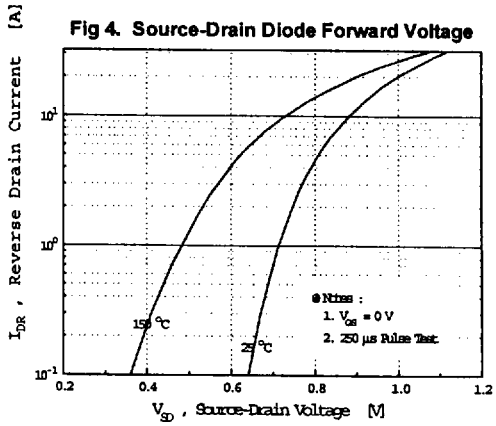


Fig 5. Capacitance vs. Drain-Source Voltage

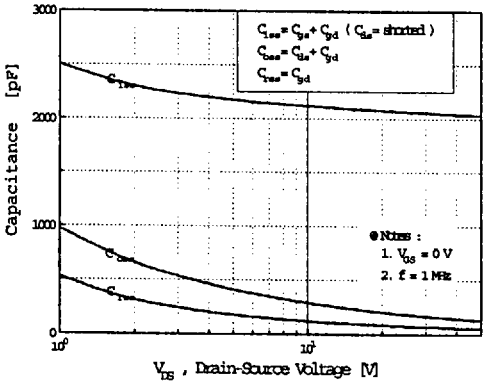


Fig 6. Gate Charge vs. Gate-Source Voltage

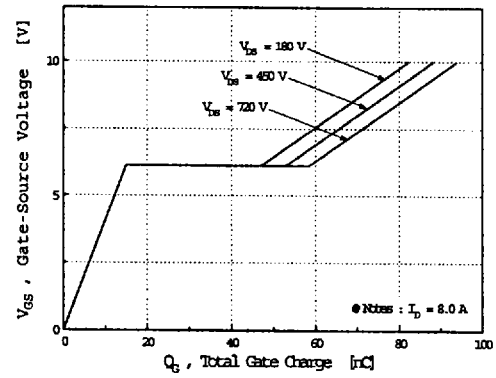


Fig 7. Breakdown Voltage vs. Temperature

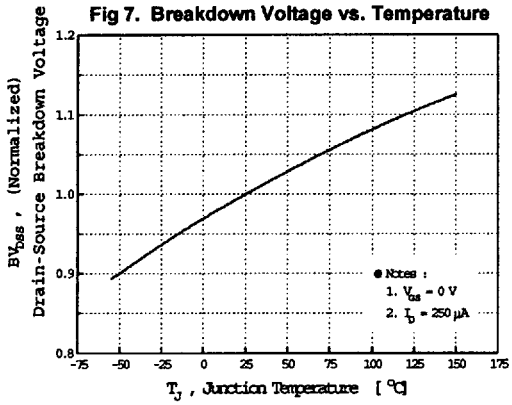


Fig 8. On-Resistance vs. Temperature

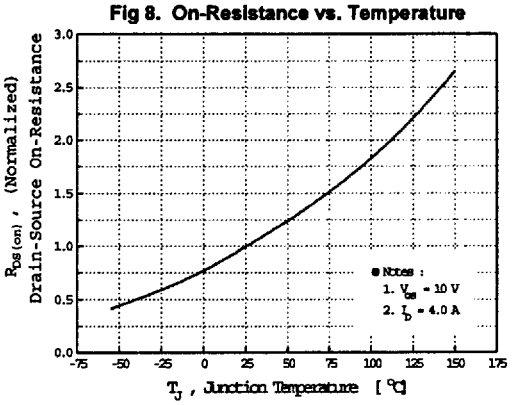


Fig 9. Max. Safe Operating Area

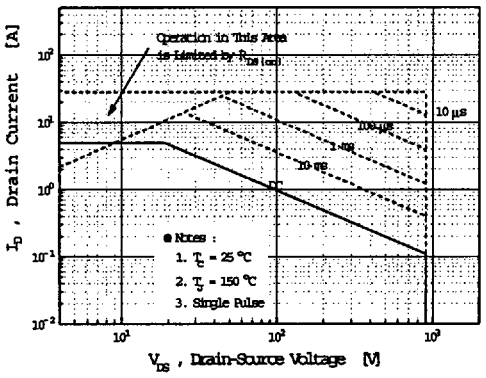


Fig 10. Max. Drain Current vs. Case Temperature

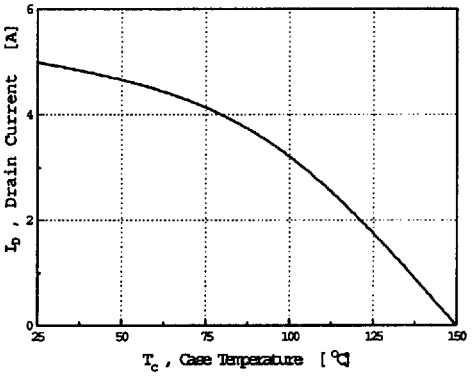


Fig 11. Thermal Response

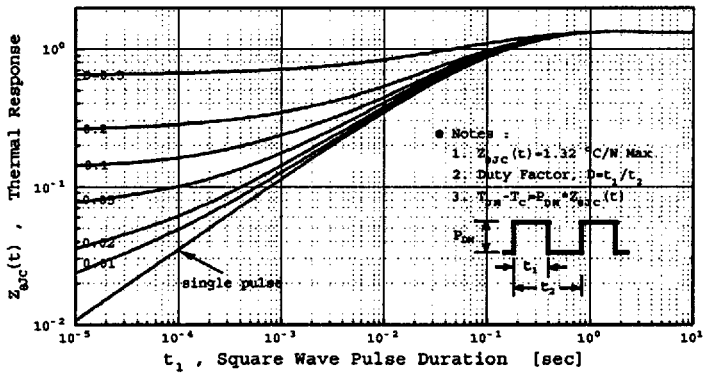


Fig 12. Gate Charge Test Circuit & Waveform

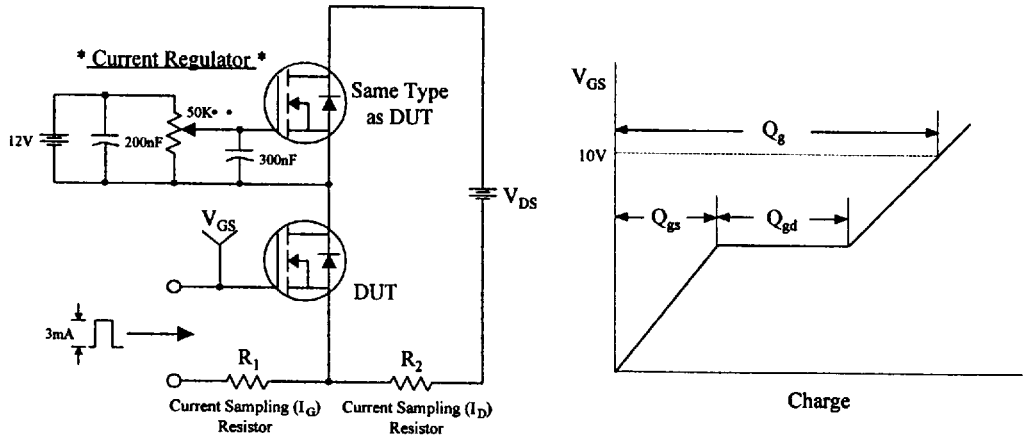


Fig 13. Resistive Switching Test Circuit & Waveforms

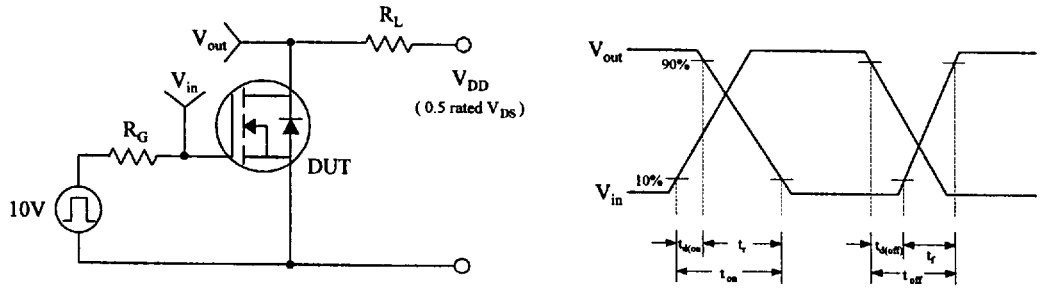


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

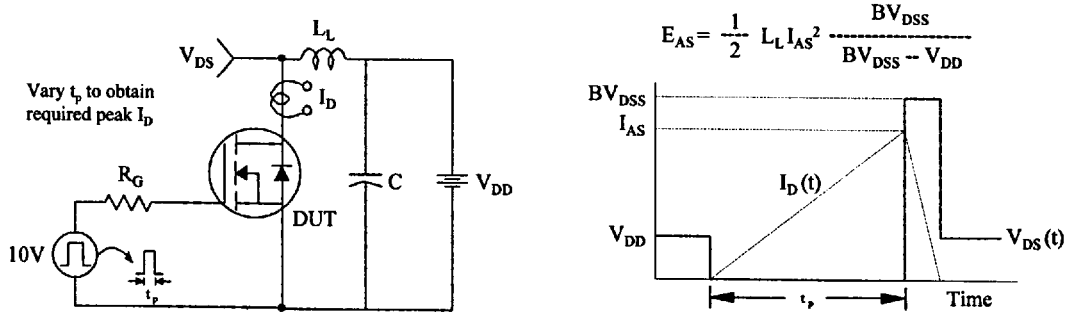
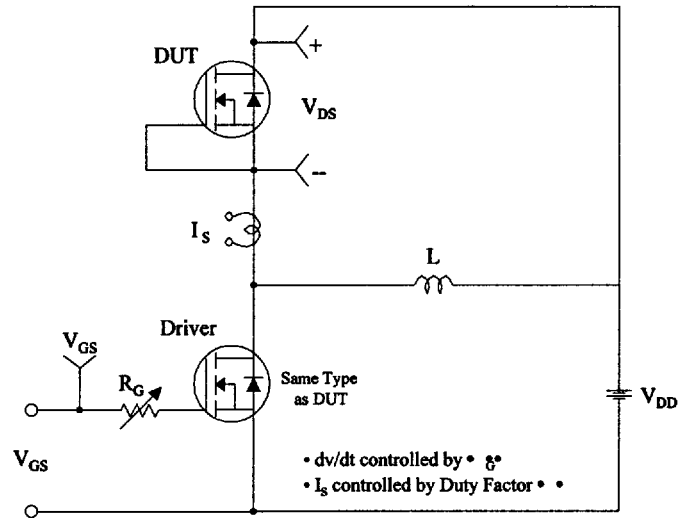
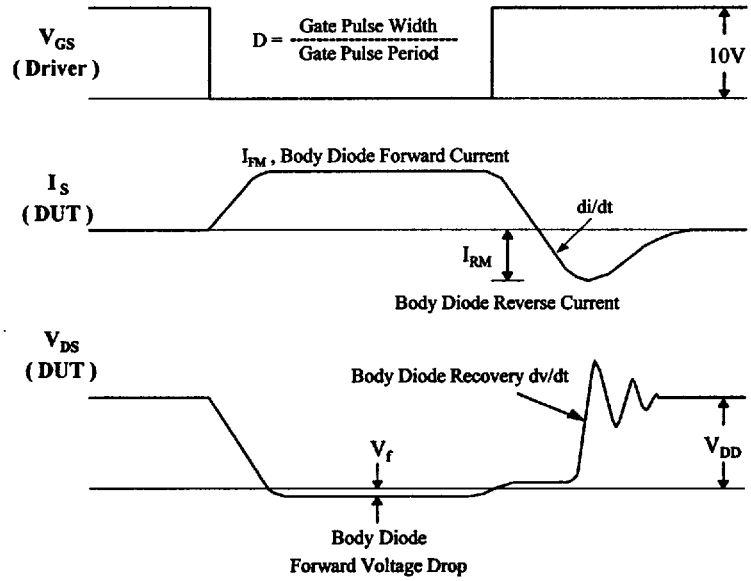
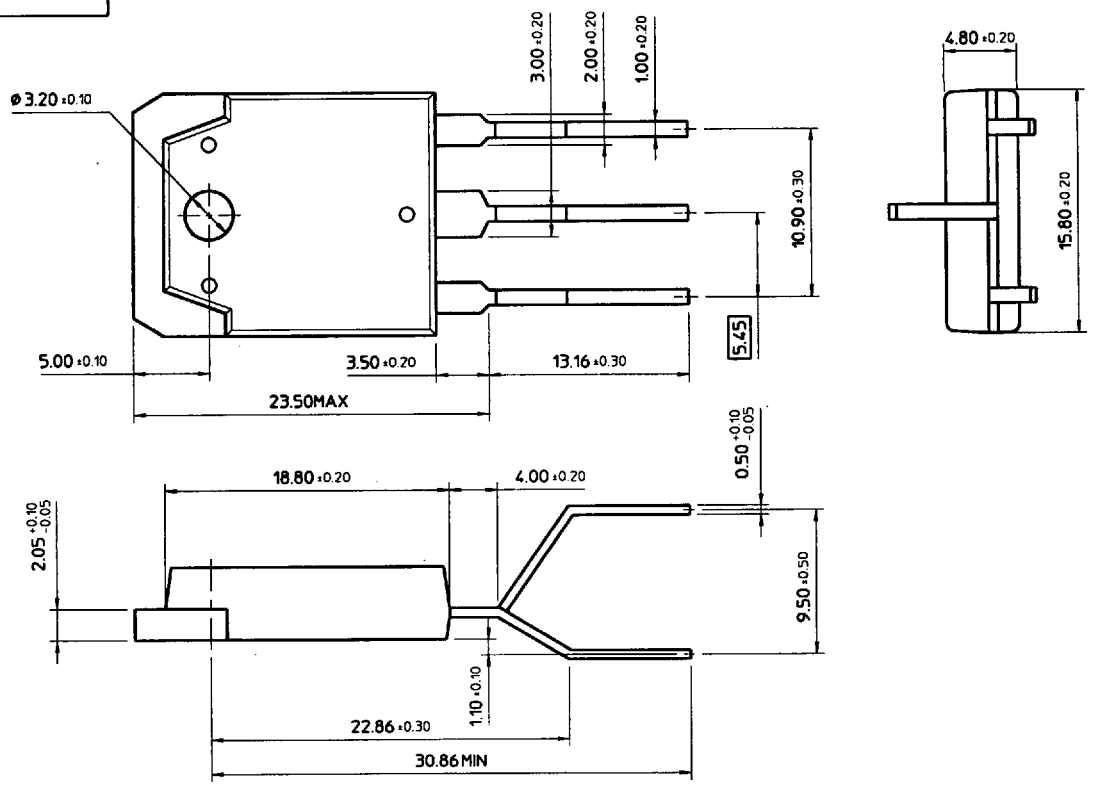


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

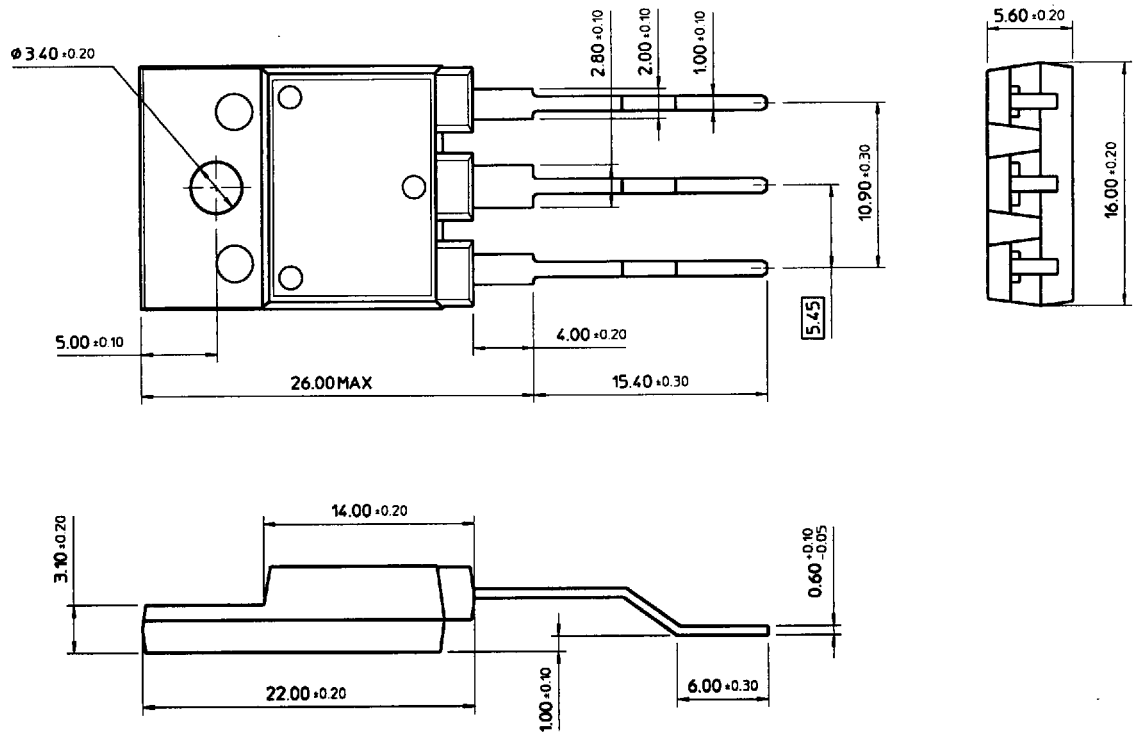




TO-3P (2)

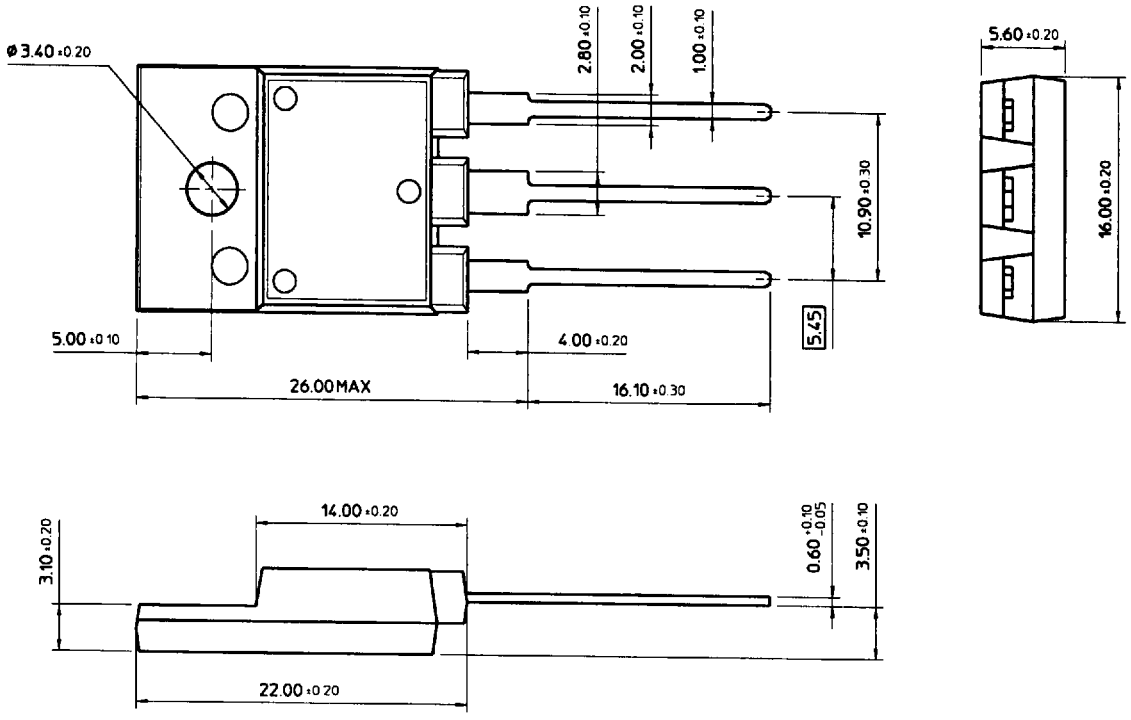


TO-3PF (1)

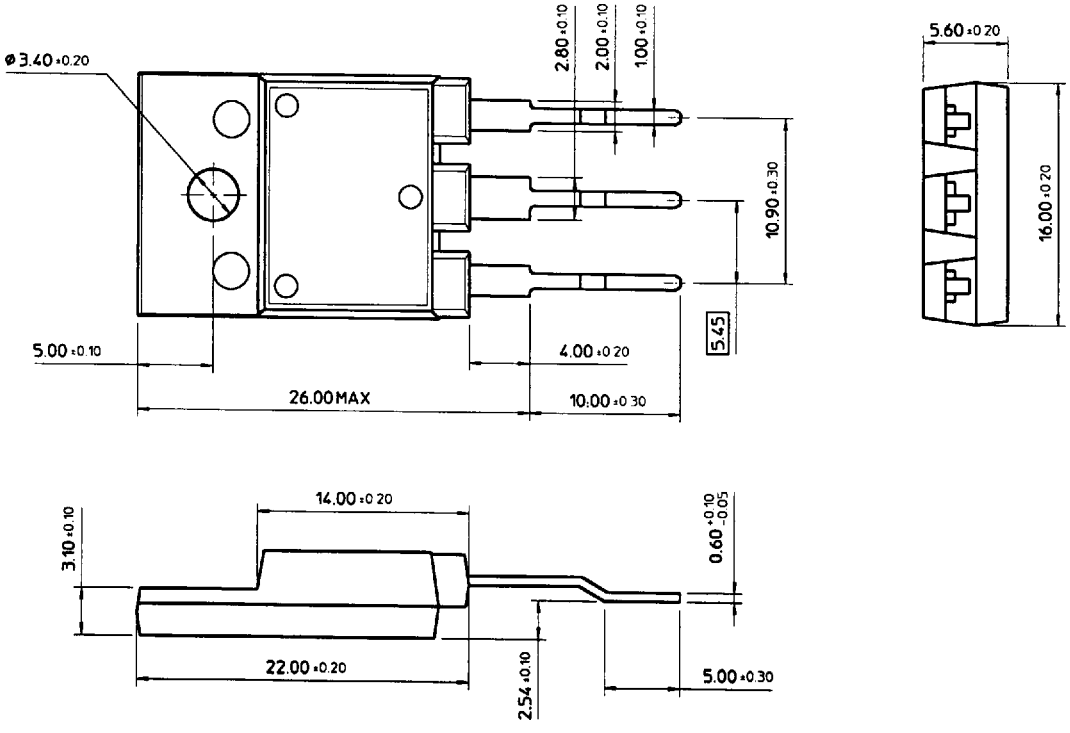


SAMSUNG ELECTRONICS

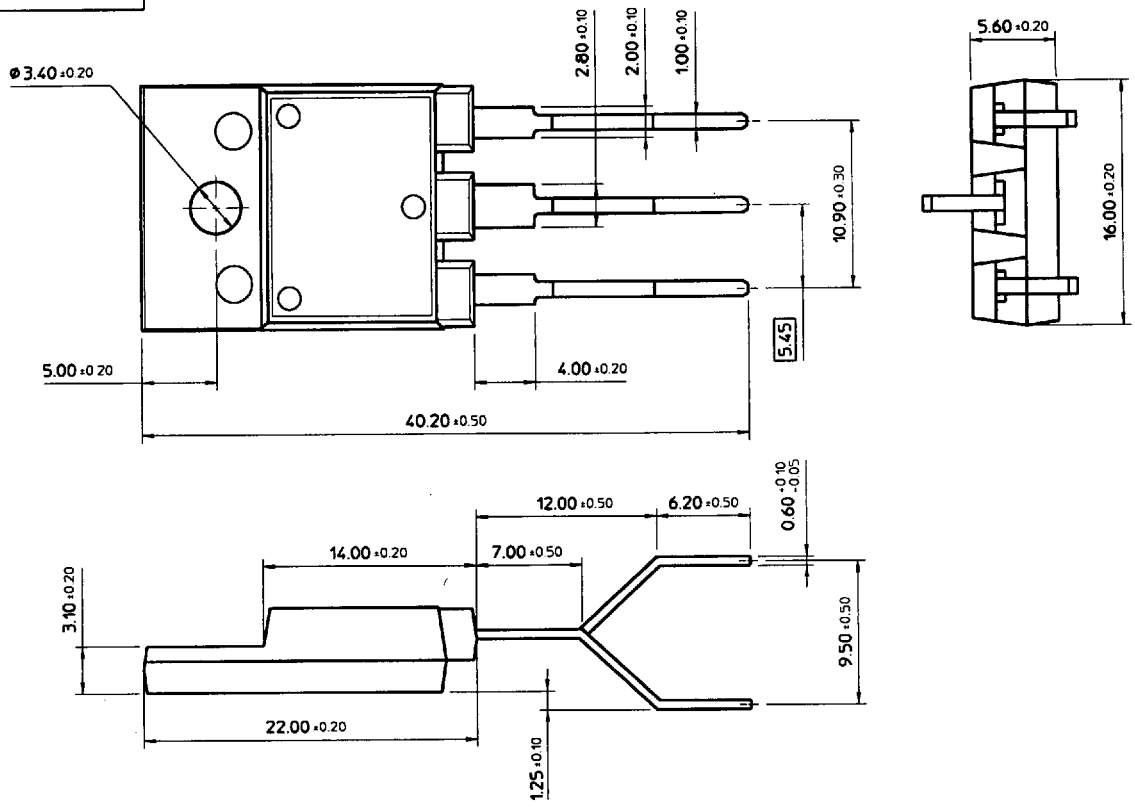
TO-3PF (2)



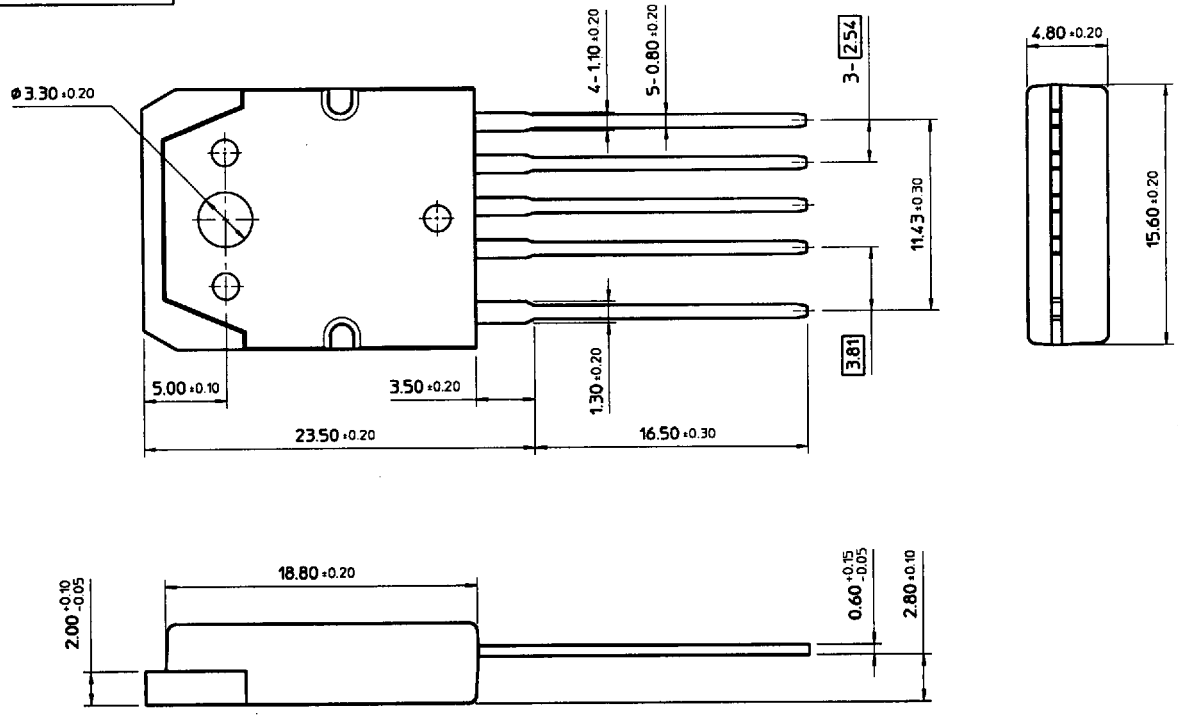
TO-3PF (3)



TO-3PF (4)



TO-3P-5L



Under Development

SAMSUNG ELECTRONICS